

FERROELECTRIC MEMORY DEVICES INCLUDING PROTECTION
ADHESION LAYERS AND METHODS OF FORMING THE SAME

ABSTRACT

A ferroelectric memory device includes an interlayer dielectric layer and a protection adhesion layer formed thereon. A buried contact extends through the protection adhesion layer and the interlayer dielectric layer. A lower electrode is on a portion of the protection adhesion layer that is adjacent to the buried contact and on the buried contact. A ferroelectric layer covers the lower electrode and the protection adhesion layer. An upper electrode overlaps the lower electrode and covers the ferroelectric layer. Related methods are also disclosed.